

The Berezinskii-Kosterlitz-Thouless Transition and Anomalous Metallic Phase in a Hybrid Josephson Junction Array

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We investigate the Berezinskii-Kosterlitz-Thouless (BKT) transition in a semiconductor-superconductor two-dimensional Josephson junction array. Tuned by an electrostatic top gate, the system exhibits separate superconducting (S), anomalous metal (M*), and insulating (I) phases, bordered by separatrices of the temperature-dependent of sheet resistance, R_s . We find that the gate-dependent BKT transition temperature falls to zero at the S-M* boundary, suggesting incomplete vortex-antivortex pairing in the M* phase. In the S phase, R_s is roughly proportional to perpendicular magnetic field at the BKT transition, as expected, while in the M* phase R_s deviates from its zero-field value as a power-law in field with exponent close to 1/2 at low temperature. An in-plane magnetic field eliminates the M* phase, leaving a small scaling exponent at the S-I boundary, which we interpret as a remnant of the incipient M* phase.

Josephson junction arrays (JJAs) have for decades provided model systems for investigating classical and quantum phase transitions with competing ground states, frustration, and complex dynamics [1, 2], 2D superconductivity [3, 4], and more recently as a basis for quantum simulation [5], quantum matter [6], and protected quantum information [7, 8]. It is generally accepted that JJAs exhibit a quantum phase transition between superconducting and insulating phases controlled by the ratio E_C/E_J of charging energy, E_C , of a single island to the Josephson energy, E_J , between neighboring islands. At the superconductor-insulator transition (SIT), the 2D sheet resistance R_s of the JJA is roughly the resistance quantum, $R_s \sim R_Q \equiv h/4e^2$ [9, 10], or equivalently, $E_C/E_J \sim 1$, with a temperature-independent separatrix at $R_s \sim R_Q$ [1, 2].

However, this conventional SIT picture misses a commonly observed regime seen in a variety of materials—the anomalous metal—where R_s saturates at low temperature at a tunable value $R_s < R_Q$ [11]. The origin and requirements for the anomalous metal are not known, despite years of investigation and speculation [11–15].

At zero magnetic field, temperature destroys 2D superconductivity through a Berezinskii-Kosterlitz-Thouless (BKT) transition, characterized by the unbinding of vortex-antivortex pairs when the temperature, T , exceeds a critical value, T_{BKT} [17–19]. Dissipation by the motion of unbound vortices above T_{BKT} results in nonzero resistivity [20, 21].

In this Letter, we experimentally investigate the interaction of the BKT transition with the anomalous metal in an InAs/Al heterostructure patterned into a regular array of micron-size Al islands separated by narrow stripes where the Al has been removed, which can be depleted by a global gate. We identify two distinct boundaries

where $R_s(T)$ curves separate, controlled by gate voltage, defining three regions of superconducting (S), anomalous metal (M*) and insulating (I) phases. A similar conclusion was recently proposed for a field-driven SIT [22, 23], and contrasts interpretations where BKT crosses to a quantum-dominated regime throughout the superconducting phase [24], or where inadequate cooling is responsible for anomalous metal behavior [25, 26].

We find that in S phase, that is, the low-resistance side of the S-M* separatrix, the temperature dependent sheet resistance, $R_s(T)$, is well described by the BKT form [20] over three orders of magnitude of R_s , yielding a gate-voltage-dependent T_{BKT} as a fit parameter. Importantly, we find T_{BKT} goes to zero at the S-M* boundary, *not* at the T -independent separatrix (our M*-I boundary) where $R_s \sim R_Q$, as one would expect for a conventional SIT [2, 27]. The observation of a vanishing T_{BKT} at the S-M* boundary suggests that the transition from M* to the normal metal (M) with increasing temperature is not BKT-like. We interpret the result as incomplete vortex-antivortex pairing that persists to zero temperature in the M* phase.

We next demonstrate power-law dependences of R_s on small perpendicular field, B_\perp , in both the S and M* phases. Linear magnetoresistance, $R_s(B_\perp, T_{\text{BKT}}) \propto B_\perp^\beta$, with $\beta = 1$, is expected around the BKT transition [28–32]. We find that in the S phase, $\beta(T) \sim 1$ near T_{BKT} , though we find $\beta(T)$ increasing with T , contrary to [28, 29]. In the M* phase, beyond where $T_{\text{BKT}} \rightarrow 0$, we again find a power law after subtracting the saturation value, $[R_s(B_\perp, T) - R_s(0, T)] \propto B_\perp^\beta$, though with $\beta < 1$, approaching $\beta = 1/2$ well into M* [see Figs. 3(b,c)].

Finally, we find that a moderate in-plane magnetic field, $B_\parallel \sim 0.5$ T, known to eliminate M* [16], causes the S-M* and M*-I phase boundaries to coalesce into to a single broad S-I boundary (Fig. 4). The broad S-I transition

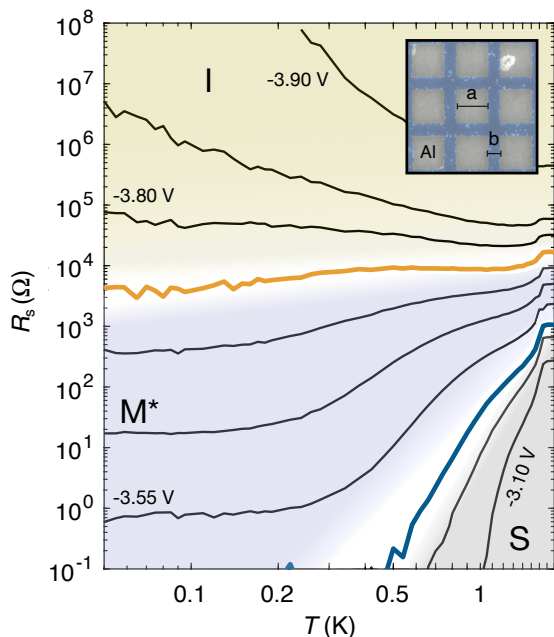


FIG. 1. Sheet resistance, $R_s(T)$, of the InAs/Al Josephson junction array (inset) as a function of temperature, T , at several gate voltages, V_G , ranging from -3.1 V to -3.9 V, from Ref. [16]. Two separatrices (blue and orange curves) mark the boundaries between superconducting (S) phase, where $R_s(T)$ is concave down, becoming unmeasurably small at low T , the anomalous metal (M^*), where $R_s(T)$ is concave up and saturating at low T , and the insulating phase, where $R_s(T)$ increases with falling T . The S- M^* boundary (blue) starts at normal-state sheet resistance, $R_N \sim 1$ k Ω . The M^* -I (orange) is roughly temperature independent, with $R_s \sim 6$ k Ω , similar to with a conventional S-I boundary. Inset: false-color electron micrograph with scale bar showing the array before the deposition of the top insulator and metallic gate, with $1 \mu\text{m}$ Al squares patterned onto an InAs substrate, as described in Ref. [16].

at $B_{\parallel} = 0.5$ T shows a small scaling exponent at low- T , a possible remnant of the M^* phase. A transition from slow and fast temperature dependence is seen toward the S side of the broad S-I transition, separated from the S-I crossing point at $R_s \sim R_Q$, presumably another vestige of the M^* phase. The JJA was fabricated using a hybrid InAs/Al heterostructure, with a 7 nm InAs quantum well separated from a 7 nm epitaxial Al surface layer by 10 nm InGaAs barrier [16]. A Hall bar was patterned by wet etching through the quantum well. A subsequent patterning of 40×100 array of $1 \mu\text{m}$ Al squares separated by 150 nm (Device A) or 350 nm (Device B) spacing was patterned by removing the Al between squares using Transene D aluminum etchant (see Fig. 1, inset). The array was then covered by a 40 nm Al_2O_3 insulating layer followed by a Ti/Au top gate. The two measured devices behaved similarly. Except where noted data are from Device A.

Devices were measured in a dilution refrigerator with

a base mixing chamber temperature of 20 mK. A vector magnet was used to independently apply perpendicular and in-plane magnetic fields applied along the current direction, after calibrating the magnet axes to compensate for small sample tilt. A four-wire measurement of longitudinal resistance with both current and voltage measured was carried out using standard AC lock-in techniques, keeping the voltage across the array below $5 \mu\text{V}$. 2D sheet resistance $R_s(T)$, spanning 0.1Ω to $100 \text{M}\Omega$, were accessible by tuning the top-gate voltage, V_G , in the range -3 V to -4 V for both devices. Over this same range, normal-state sheet resistance R_N , measured above the critical temperature $T_{c0} \sim 1.6$ K of the Al islands, spanned $R_N \sim 100 \Omega$ at $V_G \sim -3$ V to $R_N \sim 1 \text{M}\Omega$ at $V_G \sim -4$ V, as shown in Fig. 1.

The experimental phase diagram in the T - V_G plane is shown in Fig. 1, along with representative $R_s(T)$ curves at fixed V_G . In the superconducting (S) region, with $R_N \lesssim 1$ k Ω , all $R_s(T)$ curves were found to decrease with lower T down to the smallest measurable resistance, $R_s \sim 0.1 \Omega$. At more negative gate voltages, in the region marked M^* , R_s initially falls, then saturates at a V_G -dependent value ranging from $\sim 1 \Omega$ up to $\sim R_Q$. As discussed below, $R_s(T)$ curves in M^* are distinct from those in S throughout the temperature range. In particular, $R_s(T)$ in M^* is not well described by the BKT form [20]. Comparable to the conventional SIT, the M^* -I separatrix (orange curve in Fig. 1) occurs at $R_s \sim R_Q$ and is roughly independent of T from lowest measured temperature up to T_{c0} . At more negative V_G beyond the M^* -I separatrix in the region marked I, $R_s(T)$ rises with lower T , characteristic of the insulating phase. We have previously investigated variable range hopping and activated regimes of the I phase, and did not observe low- T saturation I phase away from M^* -I separatrix [16]. Note in Fig. 1 that R_N slightly exceeds $R_s(T)$ just below T_{c0} throughout the measured S, M^* , and I phases, so that the transition at T_{c0} makes a small upward step in resistance going from below to above the transitions where the islands become normal. The critical temperature for the islands, $T_{c0} \sim 1.6$ K, is independent of V_G .

Representative $R_s(T)$ curves are shown in Fig. 1. For a larger set of curves, finely sampled in V_G throughout the S and M^* phases, we fit $R_s(T)$ to the BKT form [20, 21],

$$R_s(T) = aR_N \exp \left[-b \left(\frac{T_{c0} - T}{T - T_{\text{BKT}}} \right)^{1/2} \right]. \quad (1)$$

For each V_G , a least-square fit to the logarithm of $R_s(T)$ yields a , b , and T_{BKT} as fit parameters, with $T_{c0} = 1.6$ K and $R_N(V_G)$ taken from measurements. Figure 2(a) shows a typical fit deep in the S regime, yielding excellent agreement between experimental and Eq. 1 over several orders of magnitude of $R_s(T)$ from the lowest measured resistance to R_N . The resulting T_{BKT} is indicated along the top axis. As V_G is set more negative

but still within S, the data and fits begin to deviate most noticeably for $T \lesssim 1$ K. Note that the measurement lies *below* the fit, in contrast to [24]. The extracted T_{BKT} values, marked on the top axes of Figs. 2(b,c), move quickly toward zero as the S-M* boundary is approached at more negative gate voltages.

Repeating fits across a range of gate voltages within the S region yields the values for T_{BKT} shown in Fig. 2(d), plotted as a function of R_N^{-1} , along with a classical model (absent charging effects), $T_{\text{BKT}} \propto R_N^{-1}$. We find that T_{BKT} is roughly proportional to R_N^{-1} in the S region, but deviates below the model line, reaching $T_{\text{BKT}} = 0$ at a value of $R_N(V_G) \sim 1$ k Ω , coinciding with the S-M* boundary. We emphasize that value of V_G marked as the the S-M* boundary in Fig. 2 was defined by the separatrix (blue trace) in Fig. 1, not by the point where $T_{\text{BKT}} = 0$. The observation that T_{BKT} reaches zero at the S-M* boundary is a striking experimental result, not expected within a conventional SIT picture, where $T_{\text{BKT}} \rightarrow 0$ at $R_s \sim R_Q$, i.e., the M*-I boundary in this case.

The simple proportionality $T_{\text{BKT}} = \gamma R_N^{-1}$ follows from the Ambegaokar-Baratoff relation at $T \ll \Delta$ for individual junctions, $I_c^{(i)} R_N^{(i)} = \pi \Delta / 2e$, where Δ is the superconducting gap induced in the InAs under the Al islands. Setting $R_N = R_N^{(i)}$ and $E_J = (\hbar/2e)I_c^{(i)}$ gives $E_J = (\Delta/2)(R_Q/R_N)$. The classical BKT relation, $k_B T_{\text{BKT}} = (\pi/2)E_J$ [33] can then be written $T_{\text{BKT}} = (\pi\Delta/4k_B)(R_Q/R_N)$.

An upper bound on Δ based on the critical temperature of the Al islands gives $\Delta \lesssim 1.76 k_B T_{c0} = 240 \mu\text{eV}$, using the measured $T_{c0} = 1.6$ K. A lower bound based on the $I_c R_N$ product, using the array depinning current $I_d^{(A)} = 20 \mu\text{A} \lesssim 40 I_c^{(i)}$ of the 40-junction-wide array at $R_N = 0.4$ k Ω , gives $\Delta \gtrsim 120 \mu\text{eV}$ [16]. Tunneling spectroscopy into the InAs adjacent to the Al edge in similar material yields $\Delta \sim 190 \mu\text{eV}$ [34]. Using this value gives $\gamma = (\pi\Delta/4k_B)R_Q \sim 11$ k Ω K.

Experimentally, we observe the proportionality $T_{\text{BKT}} = \gamma^{(\text{exp})} R_N^{-1}$ in the S phase, as seen in Fig. 2(d), but with a considerably smaller slope, $\gamma^{(\text{exp})} \sim 0.2$ k Ω K. We interpret the discrepancy as reflecting a suppressed BKT transition temperature, $T_{\text{BKT}} \sim 0.02 E_J$ —while keeping $E_J \sim (\Delta/2)(R_Q/R_N)$ —instead of the classical relation $T_{\text{BKT}} \sim E_J$. This interpretation is consistent with a charging energy $E_C \sim 150 \mu\text{eV}$, previously measured in the I phase [16], being comparable to E_J when $R_s \sim R_N \sim R_Q$.

As V_G becomes more negative, moving the system from the S phase toward the S-M* boundary, T_{BKT} deviates from the proportionality $T_{\text{BKT}} = \gamma R_N^{-1}$, reaching zero (roughly linearly) at the S-M* boundary, as seen in Fig. 2(d). In conventional SIT systems, reduction of T_{BKT} below $\sim E_J \propto R_N^{-1}$ is an expected and well investigated consequence of quantum corrections associated

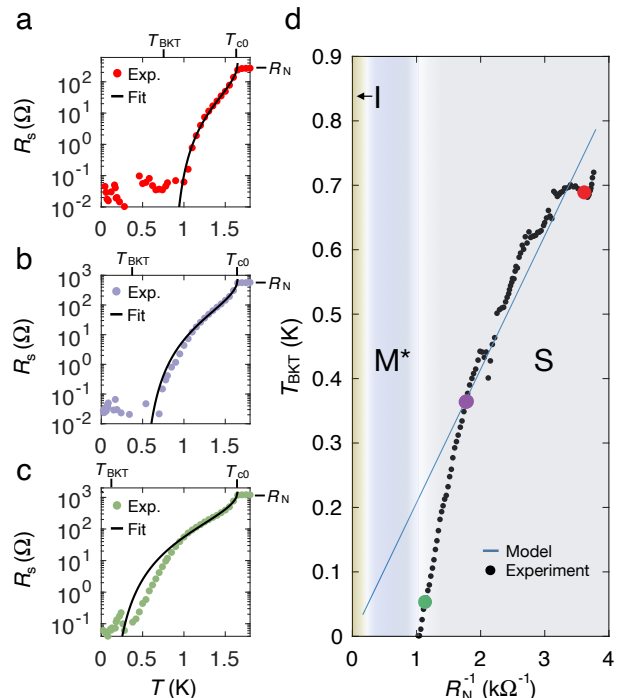


FIG. 2. (a-c) Sheet resistance, $R_s(T)$ as a function of temperature, T at three gate voltages (filled colored circles), parameterized by normal-state sheet resistance, R_N , along with fits to Eq. 1. Top axes show gate-independent critical temperature, T_{c0} of the Al squares, read directly from the data, and BKT transition temperature, T_{BKT} from the fits. Note the good fit deep in S, which becomes poorer toward the S-M* boundary. (d) BKT transition temperature T_{BKT} extracted from fits at many gate voltages (black filled circles), as a function of R_N^{-1} . T_{BKT} reaches zero near the S-M* boundary, defined by the blue separatrix in Fig. 1. Three colored data points correspond to panels a-c. Model line is based on linear relations $T_{\text{BKT}} \sim E_J \propto I_c \propto R_N^{-1}$, with a single fit parameter (see text).

with island capacitance [1, 2, 35, 36]. However, in the conventional case, the suppressed T_{BKT} reaches zero at the SIT, where $R_N \sim R_Q$. In the present case, one might have expected a deviation of T_{BKT} to reach zero at the corresponding M*-I separatrix where $R_s \sim R_N \sim R_Q$, but that is not what is observed. Instead, we find that T_{BKT} reaches zero at the S-M* boundary, and that $T_{\text{BKT}} = 0$ throughout the M* phase.

These observation, the 50-fold reduction in slope of T_{BKT} versus R_N^{-1} in the S phase and the vanishing of T_{BKT} in the M* phase, suggest a picture of vortex-antivortex binding that is suppressed in S and fails in M*. As discussed below, this picture is consistent with the observed scaling in M* of R_s with small perpendicular magnetic field.

The observed vanishing of T_{BKT} at the S-M* boundary is consistent with another method of determining T_{BKT} : a jump in the voltage-current characteristic, $V \propto I^\zeta$,

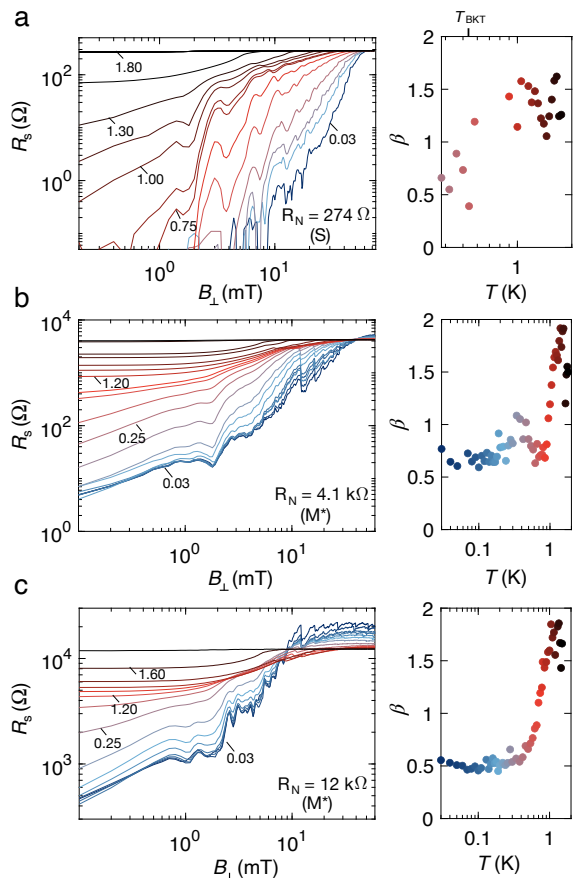


FIG. 3. Low-field magnetoresistance $R_s(B_\perp, T)$ as a function of perpendicular magnetic field, B_\perp , shows a power-law dependence (straight line on a log-log plot), $R_s(B_\perp, T) - R_s(0, T) = A(T)B_\perp^{\beta(T)}$ with a power $\beta(T)$ dependence on temperature, T (marked on graphs), and gate-controlled normal-state sheet resistance, R_N . (a) In the superconducting (S) phase, on the low-resistance (less negative V_G) side of the S-M* boundary, with $R_N = 274 \Omega$, $\beta(T_{\text{BKT}}) \sim 1$. (b-c) In M*, $\beta(T) < 1$ at low T , and appears to settle around $\beta \sim 1/2$. Fluctuations in $R_s(B_\perp)$ on a ~ 1 mT scale result from flux commensuration effects.

from ohmic, $\zeta = 1$, for $T > T_{\text{BKT}}$ to $\zeta = 3$ at $T = T_{\text{BKT}}$. The condition $\zeta = 3$ is equivalent to the point where $R_s (\propto dV/dI \propto V^{\zeta-1})$ first touches zero at its minimum at zero bias. Because R_s is an even function of I , when it first touches zero it will in general be parabolic to lowest order, $R_s \propto I^2$, which is equivalent to $V \propto I^3$. Throughout M*, the nonzero R_s down to the lowest temperatures implies ohmic response, $\zeta = 1$. The condition $\zeta = 3$ is never reached in M*, consistent with $T_{\text{BKT}} = 0$.

By the same argument, now in the S phase, T_{BKT} is roughly where $R_s (\propto V^{\zeta-1})$ first touches zero. That is, R_s will be parabolic ($\zeta - 1 \sim 2$) at T_{BKT} . Below T_{BKT} , dV/dI will be a flat-bottomed, even function around zero bias, giving $\zeta \geq 5$. Above T_{BKT} , the ohmic R_s gives $\zeta = 1$. This implies a jump from $\zeta = 1$ to $\zeta \sim 3$ at T_{BKT} in the S phase.

We next examine magnetoresistance $R_s(B_\perp)$ at small perpendicular magnetic field, B_\perp , which has been investigated previously to identify the BKT transition in arrays and 2D films. Conventional SITs [29, 37, 38] and anomalous metals [22, 23, 32, 39] often show a power-law dependence, $R_s(B_\perp, T) - R_s(0, T) = A(T)B_\perp^{\beta(T)}$, in some cases consistent the BKT prediction, $\beta(T_{\text{BKT}}) = 1$ [29, 32, 37]. Other experiments [38] find $\beta(T) > 1$, consistent with activated vortex creep with logarithmic vortex interactions [40]. In systems exhibiting anomalous metal behavior [$R_s(0, 0) \neq 0$], magnetic field dependence of the low- T saturating resistance was observed to be activated [41] or power-law with $1 < \beta(T) < 3$ in MoGe films [42] and crystalline NbS₂ [39]. In higher-resistance granular InO₂ films, smaller exponents were found, $\beta(T \rightarrow 0) = 0.66$ [22] and $\beta(T \rightarrow 0) = 0.45$ [23] in granular films. Reference [43] reports $\beta(T) \sim 2$, also consistent with [42], though their lowest temperature data appears to show $\beta(T) < 1$.

Figure 3 shows $R_s(B_\perp, T)$ at several temperatures, in the S and M* phases, along with best-fit values for $\beta(T)$ for each T to the form $R_s(B_\perp, T) - R_s(0, T) = A(T)B_\perp^{\beta(T)}$, with prefactor $A(T)$. The power-law can be seen at the lowest fields, less than one flux quantum per plaquette [$(h/2e)(a+b)^{-2} \sim 2$ mT, see Fig. 1 inset], modulated by flux-commensuration effects above ~ 2 mT. In the S phase [Fig. 3(a)], $\beta(T) \sim 1$ for $T \sim T_{\text{BKT}} \sim 0.5$ K, roughly consistent with results in Fig. 2(d) for similar R_N . We note without explanation that the trend of increasing $\beta(T)$ with temperature is opposite of the trend reported in [29]. In the S phase, $R_s(B_\perp)$ for $T < T_{\text{BKT}}$ is below the experimental noise floor.

Throughout the M* phase, where $T_{\text{BKT}} = 0$, we find $\beta(T) < 1$ at low-temperatures (noting a bump to $\beta \sim 1$ around 0.5 K in Fig. 3(b), close the S-M* boundary). Near the M*-I border, $\beta \sim 1/2$ for a broad range of temperatures similar to [23, 43].

We speculate that the observed β reflects incomplete binding of vortex-antivortex pairs in M*. Within this picture, the value of coupling constant $K = J/k_B T$ where vortex-antivortex pairs form, but fail to bind, is $1/\pi$ [18, 44]. Then, the relation $\beta = \pi K/2$ [29] gives $\beta = 1/2$. In the S phase, on the other hand, vortex-antivortex pairs bind at T_{BKT} , giving $\beta = 1$.

Applying an in-plane magnetic field, B_\parallel suppresses the M* phase, restoring a conventional SIT, though with a small and field-dependent scaling exponent, as shown in Fig. 4. In Ref. [16], we speculated that the suppression of the M* phase with in-plane field results from increased dissipation from the soft superconducting gap, which stabilizes phase fluctuations, in this case caused by the softening of the induced gap by the in-plane field [34, 45]. This interpretation differs from Ref. [12], which found that galvanic (though not capacitive [46]) coupling to a

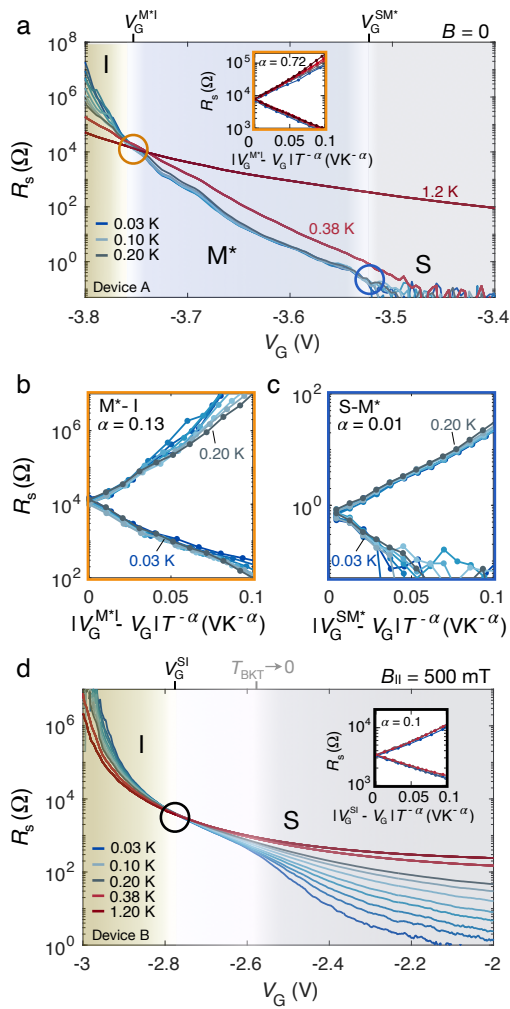


FIG. 4. (a) Sheet resistance, R_s , as a function of gate voltage, V_G at $B_{\parallel} = B_{\perp} = 0$ shows T -independent curves at low T across the anomalous metal phase, M^* , which flair out for different T in the superconducting (S) and insulating (I) phases. Inset: Scaling using only high- T isotherms ($T > 0.2$ K) at the M^* -I boundary (orange circle in main panel) yields exponent $\alpha = 0.72$. (b) Scaling using only low- T isotherms ($T < 0.2$ K) at the M^* -I boundary yields $\alpha = 0.13$. (c) Scaling at the S- M^* boundary [blue circle in (a)], yields $\alpha = 0.01$. (d) Applying an in-plane magnetic field, $B_{\parallel} = 0.5$ T, results in a single crossing of isotherms (black circle). Inset: Scaling with all isotherms yields $\alpha = 0.1$. We interpret the small α , i.e., nearly parallel isotherms, as a vestige of M^* , where low- T isotherms coincide. The broad S-I transition (white region) is bounded by the crossing point on the I side and the rapid spreading of isotherms on the S side. The top axis indicates where $T_{\text{BKT}} \rightarrow 0$ following similar analysis to Fig. 2. Data for Device B.

dissipative channel induces rather than suppressed the anomalous metal phase. Stabilization of superconductivity with in-plane field has been reported in a variety of 2D systems, including $\text{LaAlO}_3/\text{SrTiO}_3$ interfaces [47] as well as Pb [47, 48] and WTe_2 [49] thin films. Stabilization of superconductivity by an in-plane field has been

attributed to mechanisms besides dissipation, including the compensation [50] and freezing [51] of magnetic impurities. Similar stabilization of superconductivity by an applied magnetic field was also found in 1D nanowires, where it was also attributed to dissipation induced by the applied field [52, 53]. Scaling analysis for conventional SITs can be applied to a gate-voltage controlled transition using the scaled voltage axis, $|V_G^{S-I} - V_G|T^{-\alpha}$, with scaling exponent $\alpha = (z\nu)^{-1}$ where ν and z are spatial and dynamical exponents [2, 16]. Using B_{\parallel} to eliminate the M^* phase, we examine $\alpha(B_{\parallel})$ of the S- M^* , M^* -I (Fig. 4(a-c)) and S-I (Fig. 4(d)) transitions. For the M^* -I transition (orange circle) using only higher temperature data ($T > 0.2$ K) yields $\alpha = 0.72$ consistent with classical percolation, $z\nu = 4/3$ [16] while low- T scaling (Fig. 4(b)), yields $\alpha = 0.13$. Scaling at the S- M^* boundary, (blue circle), defined by the S- M^* separatrix in Fig. 1, coinciding with the value of V_G where $T_{\text{BKT}} \rightarrow 0$, also yields a small value, $\alpha(B_{\parallel} = 0) = 0.01$ (Fig. 4(c)). The reduced value of α is not surprising since within the M^* phase, $dR_s/dT \rightarrow 0$ which yields $\alpha \rightarrow 0$ on the M^* side of the transition.

Applying an in-plane field causes the S- M^* and M^* -I boundaries to coalesce, eliminating a clear M^* phase (Fig. 4(d)). Scaling at the remaining single crossing of isotherms yields a small exponent $\alpha(B_{\parallel} = 0.5\text{T}) \sim 0.10$. At the extended S-I crossing at nonzero B_{\parallel} isotherms diverge only weakly. The single crossing in Fig. 4(d) is the remnant of the M^* -I crossing at $B_{\parallel} = 0$ [orange circle in Fig. 4(a)], where low- T isotherms diverge on the I side but remain parallel in M^* , only to diverge again at the remote S- M^* boundary (blue circle). We do not interpret the small α as a Griffiths transition [54–56], though cannot rule it out. Rather, we interpret the small α as a vestige of the M^* phase, where α vanishes on the M^* sides of the S- M^* and M^* -I boundaries.

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